

General Description

The MY3400A is the high cell density trenched N-CH MOSFET, which provides excellent $R_{DS(ON)}$ and efficiency for most of the small power switching and load switch applications.

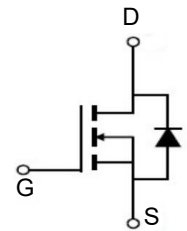
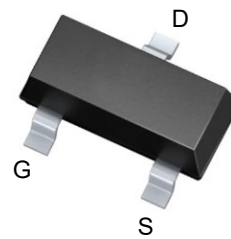


Features

V_{DSS}	30	V
I_D	5.8	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	<24	m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	<28	m Ω

Application

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY3400A	SOT-23-3L	X0BR	3000

Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	6.0	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V ¹	4.2	A
I_{DM}	Pulsed Drain Current ²	23.4	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	92	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Case ¹	---	---	$^{\circ}C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{BS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	0.9	1.4	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =10V, I _D =4.2A	-	20	24	mΩ
		V _{GS} =4.5V, I _D =4A	-	24	28	
		V _{GS} =2.5V, I _D =1A	-	35	50	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	602	-	pF
C _{oss}	Output Capacitance		-	56	-	pF
C _{rss}	Reverse Transfer Capacitance		-	42	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I=4A, V _{GS} =4.5V	-	4.8	-	nC
Q _{gs}	Gate-Source Charge		-	1.2	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	1.7	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =4A, R _{GEN} =3Ω, V _{GS} =4.5V	-	12	-	ns
t _r	Turn-on Rise Time		-	52	-	ns
t _{d(off)}	Turn-off Delay Time		-	17	-	ns
t _f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	6.0	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	23.2	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =5.8A	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Electrical and Thermal Characteristics

Figure 1 : Output Characteristics

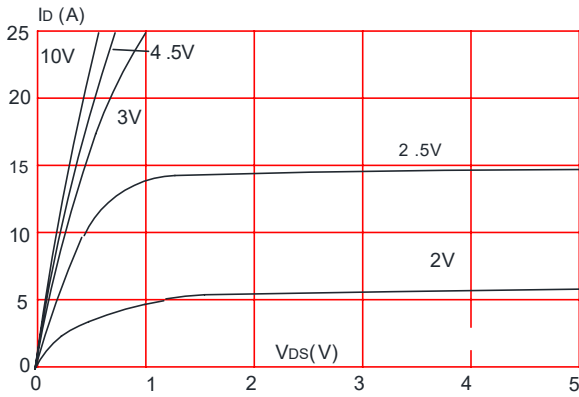


Figure 2 : Typical Transfer Characteristics

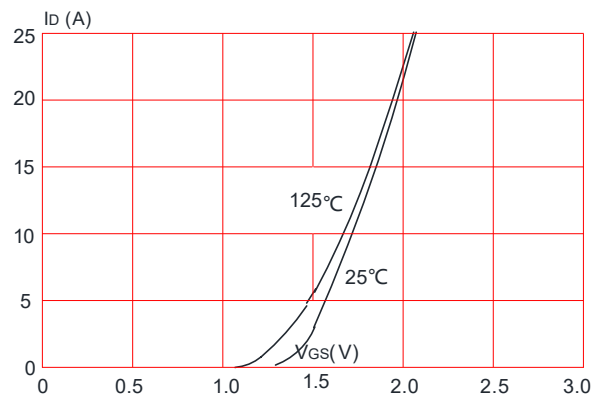


Figure 3 : On-resistance vs . Drain Current

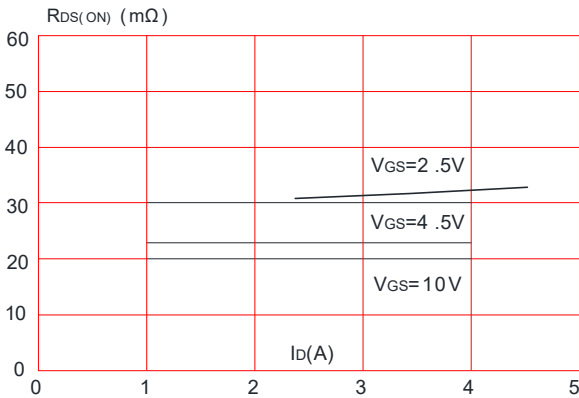


Figure 4 : Body Diode Characteristics

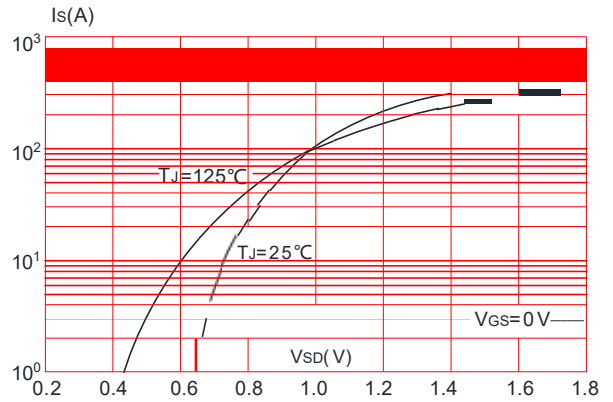


Figure 5 : Gate Charge Characteristics

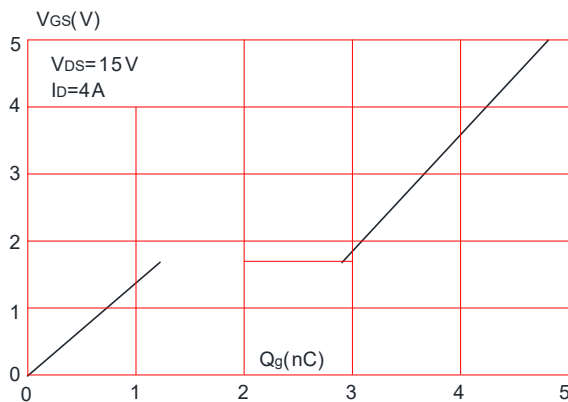


Figure 6 : Capacitance Characteristics

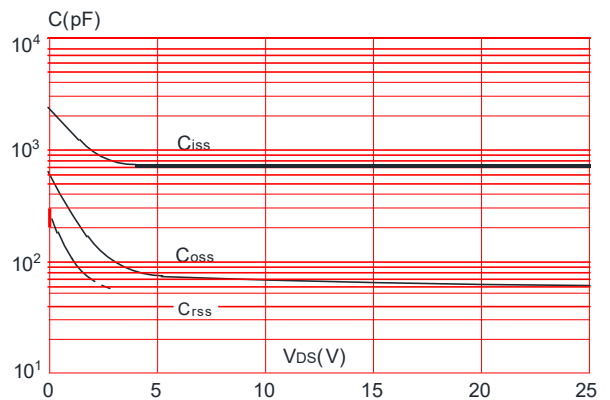


Figure 7 : Normalized Breakdown Voltage vs . Junction Temperature

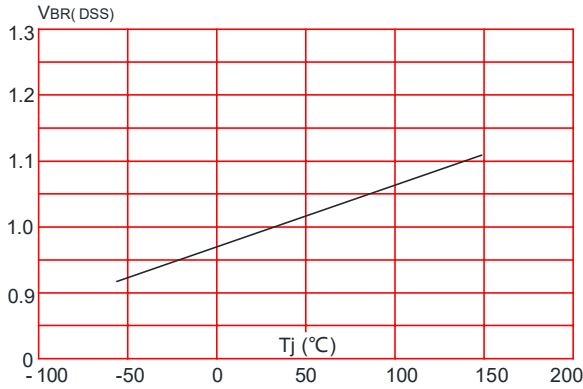


Figure 8: Normalized on Resistance vs . Junction Temperature

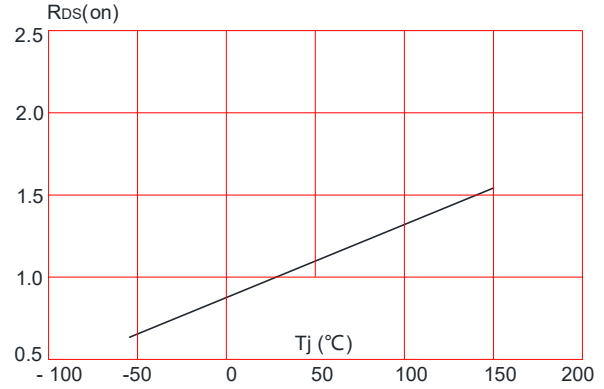


Figure 9: Maximum Safe Operating Area

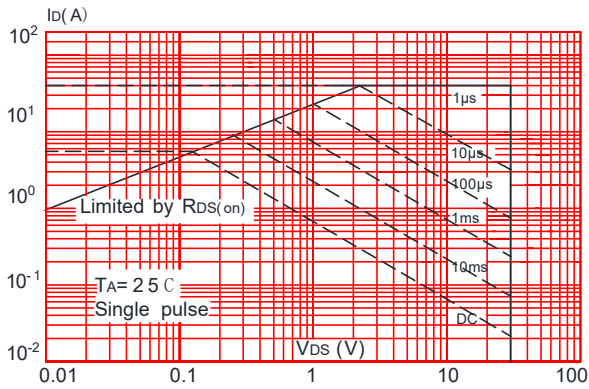


Figure 10: Maximum Continuous Drain Current vs . Case Temperature

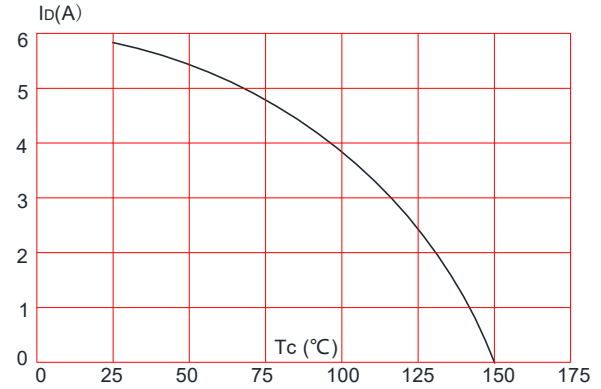
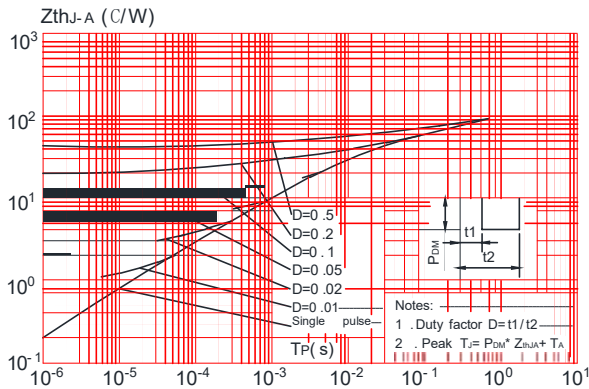
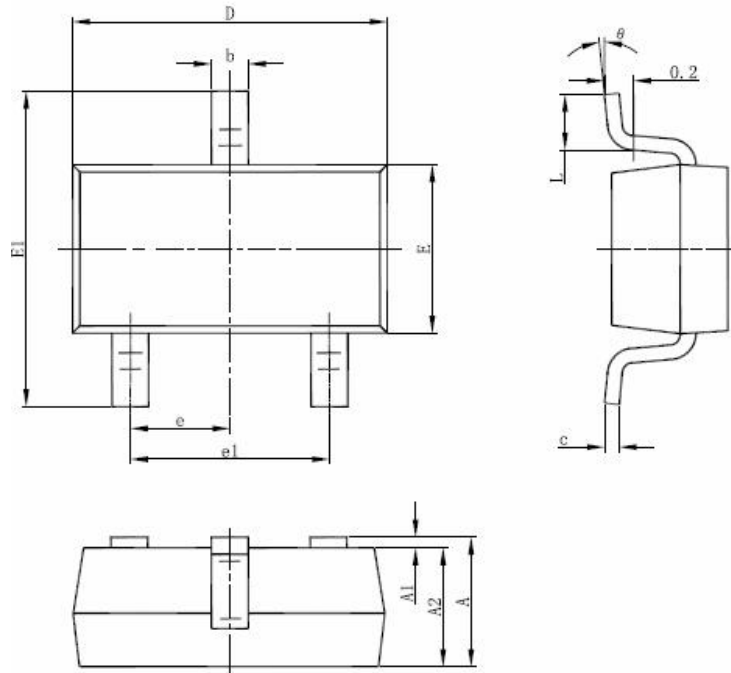


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data-SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°